

Abstract:

A device is provided. The device includes a substrate, an inorganic layer disposed over the substrate, and an organic layer disposed on the inorganic conductive or semiconductive layer, such that the organic layer is in direct physical contact with the inorganic conductive or semiconductive layer. The substrate is deformed such that there is a nominal radial or biaxial strain of at least 0.05 % relative to a flat substrate at an interface between the inorganic layer and the organic layer. The nominal radial or biaxial strain may be higher, for example 1.5%. A method of making the device is also provided, such that the substrate is deformed after the inorganic layer and the organic layer are deposited onto the substrate.